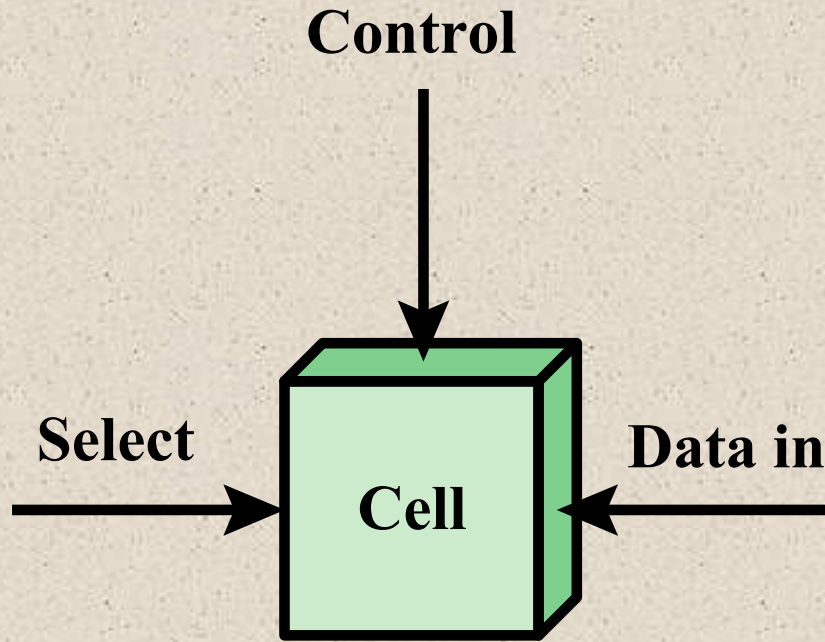
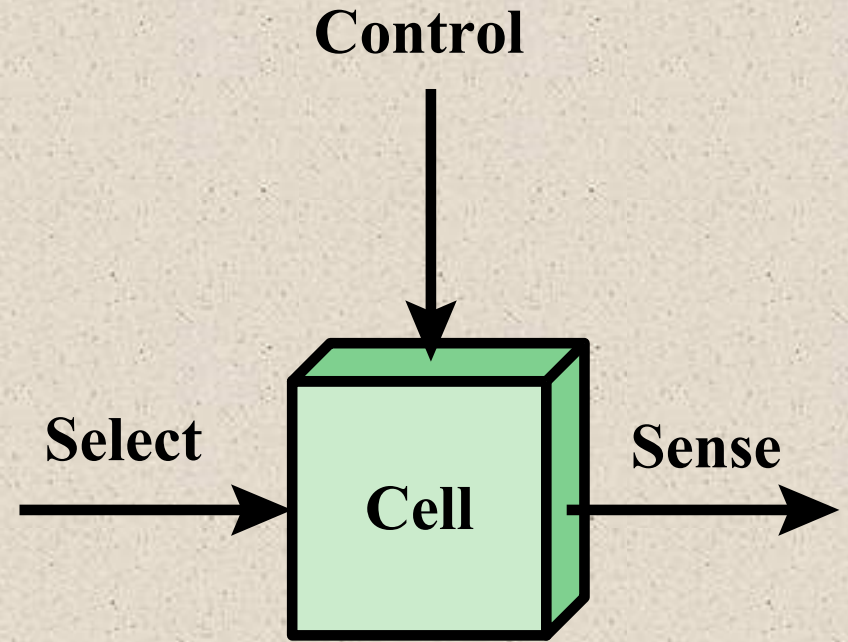




# William Stallings Computer Organization and Architecture 10<sup>th</sup> Edition



**(a) Write**



**(b) Read**

**Figure 5.1 Memory Cell Operation**



Memory Type	Category	Erasure	Write Mechanism	Volatility
Random-access memory (RAM)	Read-write memory	Electrically, byte-level	Electrically	Volatile
Read-only memory (ROM)	Read-only memory	Not possible	Masks	Nonvolatile
Programmable ROM (PROM)				
Erasable PROM (EPROM)		UV light, chip-level		
Electrically Erasable PROM (EEPROM)		Electrically, byte-level		
Flash memory		Electrically, block-level		

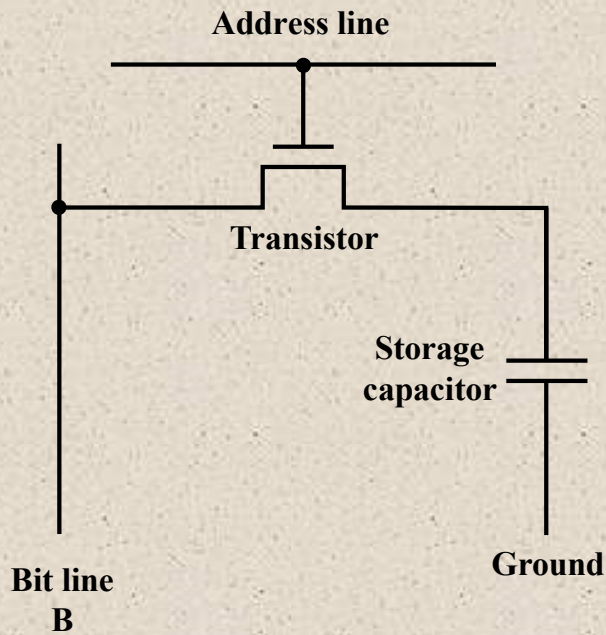
**Table 5.1**  
**Semiconductor Memory Types**



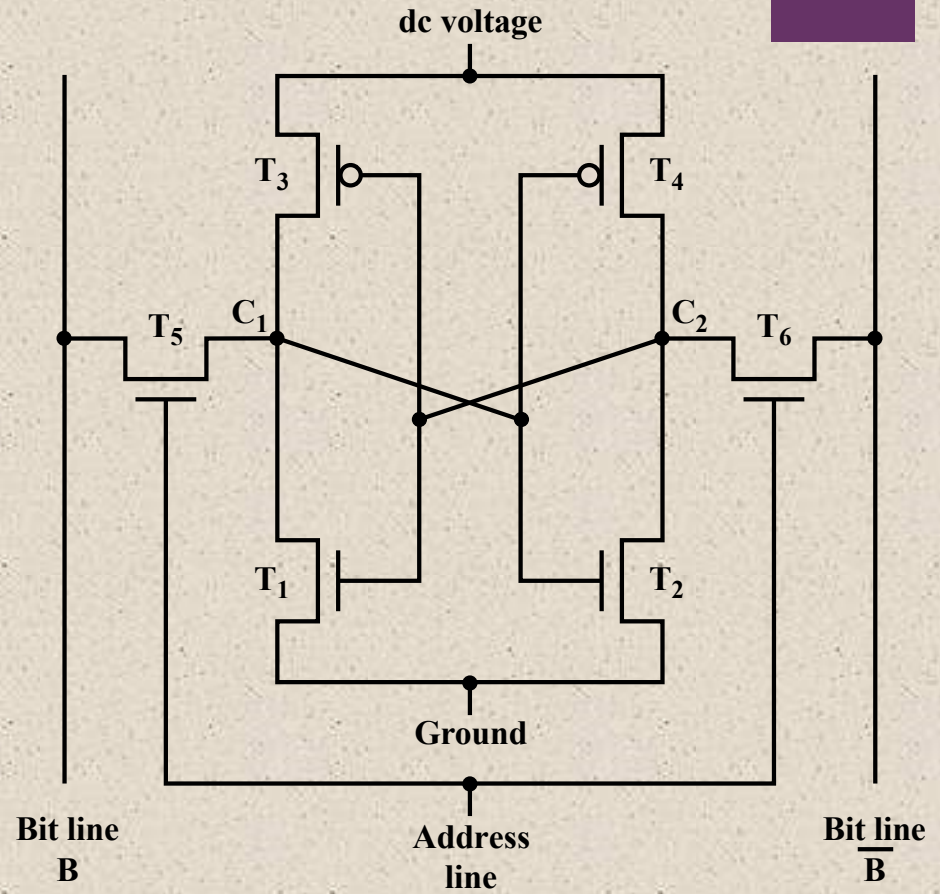
# Dynamic RAM (DRAM)



- RAM technology is divided into two technologies:
  - Dynamic RAM (DRAM)
  - Static RAM (SRAM)
- DRAM
  - Made with cells that store data as charge on capacitors
  - Presence or absence of charge in a capacitor is interpreted as a binary 1 or 0
  - Requires periodic charge refreshing to maintain data storage
  - The term *dynamic* refers to tendency of the stored charge to leak away, even with power continuously applied



(a) Dynamic RAM (DRAM) cell



(b) Static RAM (SRAM) cell

**Figure 5.2 Typical Memory Cell Structures**





# Static RAM (SRAM)

- Digital device that uses the same logic elements used in the processor
- Binary values are stored using traditional flip-flop logic gate configurations
- Will hold its data as long as power is supplied to it

